

ABSTRACT

A field effect transistor comprises a SiC substrate 1, a source 3a and a drain 3b formed on the surface of the SiC substrate 1, an insulating structure comprising an AlN layer 5 formed in contact with the SiC surface and having a thickness of one molecule-layer or greater, and a SiO₂ layer formed thereon, and a gate electrode 15 formed on the insulation structure. Leakage current can be controlled while the state of interface with SiC is maintained in a good condition.